

Supporting Information

In-situ growth of Silver Bismuth Sulfide Nanorod Arrays and Application to Solar Cells

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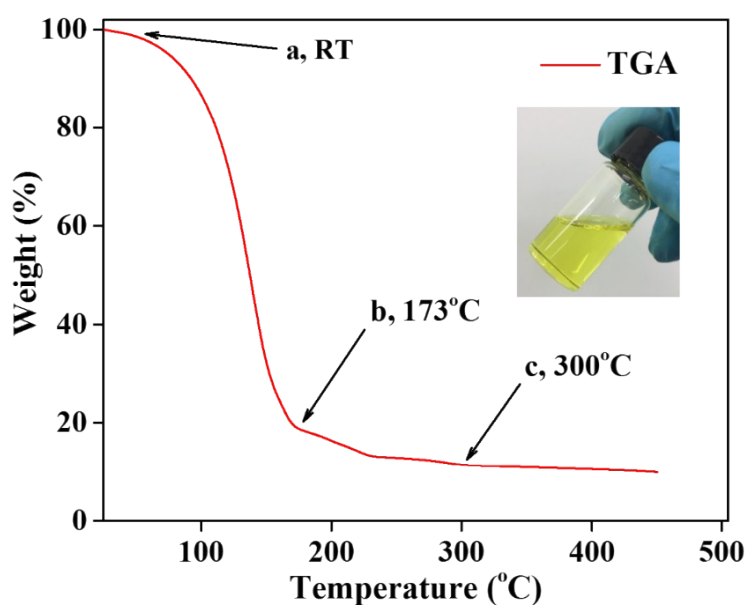


Fig. S1 TGA curve obtained by in situ drying of the AgBiS₂ precursor solution. The concentration of AgBiS₂ precursor is 0.4M. From a to b, the weight was about 80% which equalled to the evaporation of solvent DMSO. The AgBiS₂ precursor decomposition and the thiourea evaporation/decomposition lead to the weight loss from b to c, about 10% remained at the flat range. Inset: a picture of AgBiS₂ precursor solution.

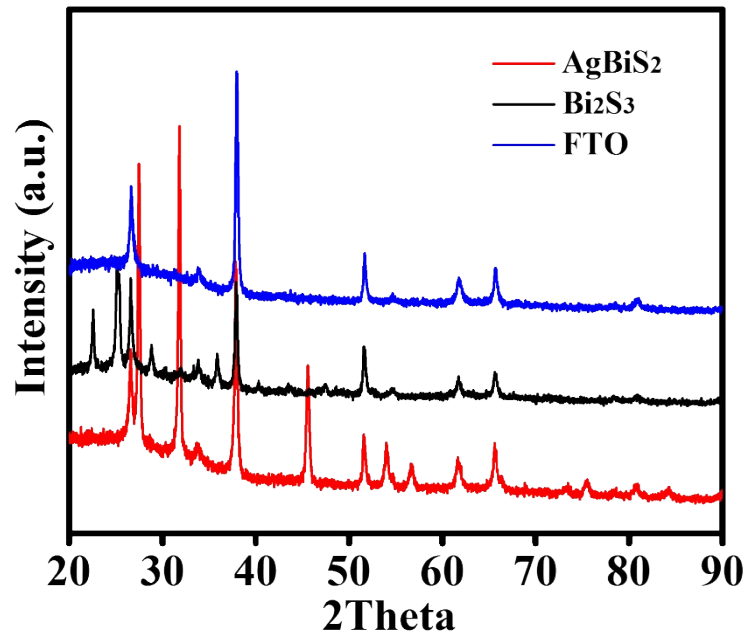


Fig. S2 XRD of AgBiS₂, Bi₂S₃ and FTO.

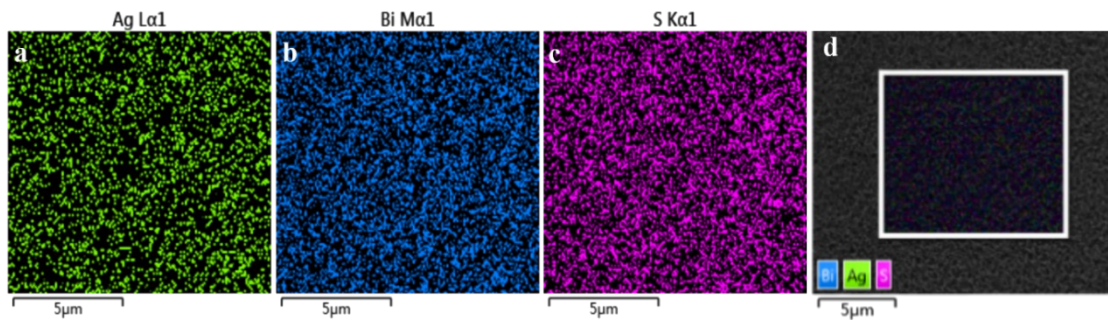


Fig. S3 EDX elemental mapping images of a) Ag, b) Bi, c) S corresponding to the white line square area in (d).

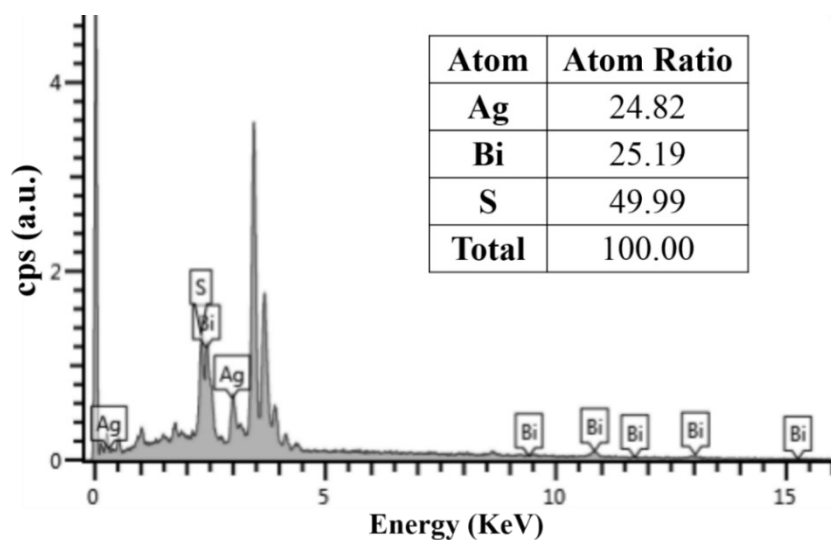


Fig. S4 EDX spectrum of the AgBiS₂ nanorod-array film.

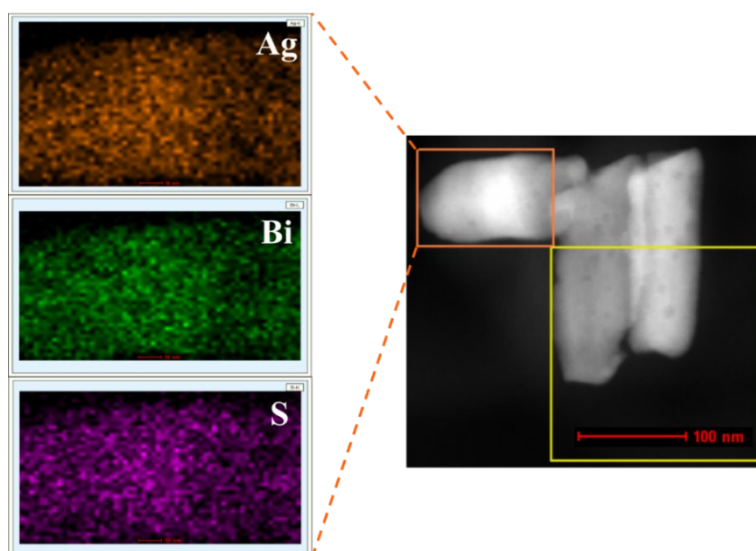


Fig. S5 TEM-EDX distribution mapping for Ag, Bi, and S in an AgBiS₂ single nanorod.

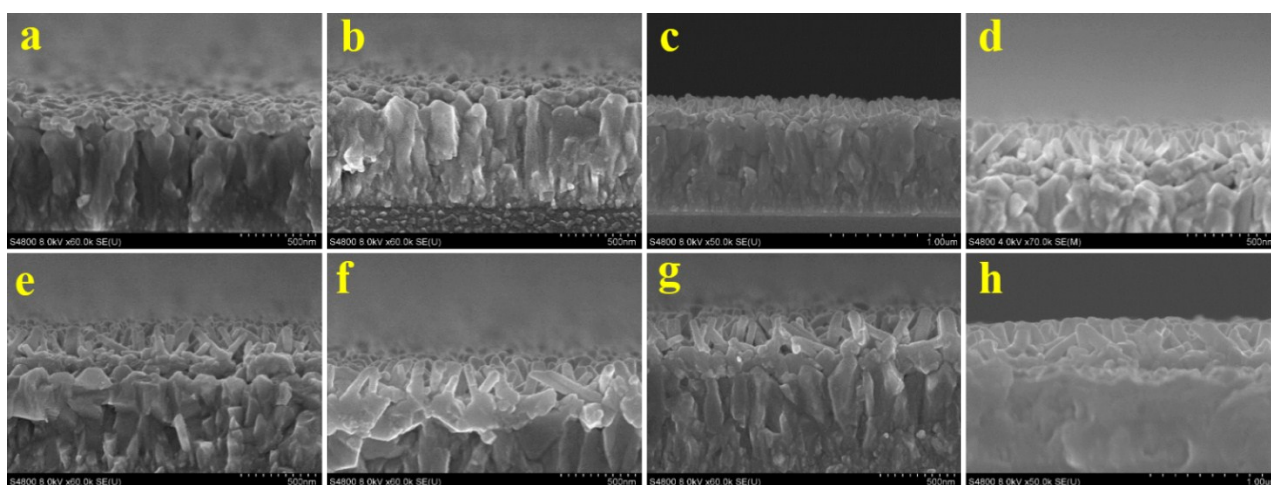


Fig. S6 Cross-sectional SEM images of different spin loops for AgBiS₂ film on FTO: a) to h) corresponding to 1 spin loop to 8 spin loops.

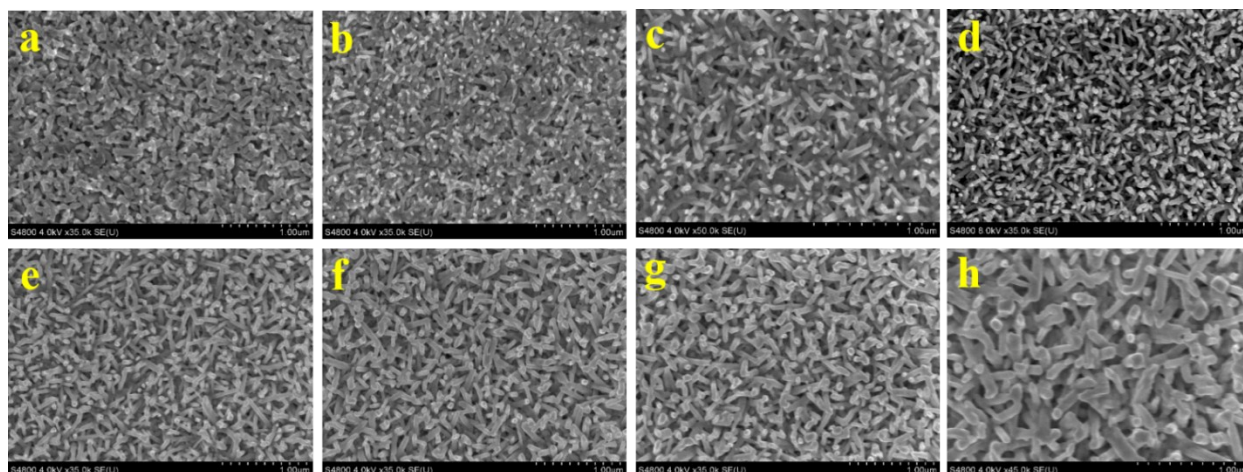


Fig. S7 Top-view SEM images of different spin loops for AgBiS₂ film on FTO: a) to h) corresponding to 1 spin loop to 8 spin loops.

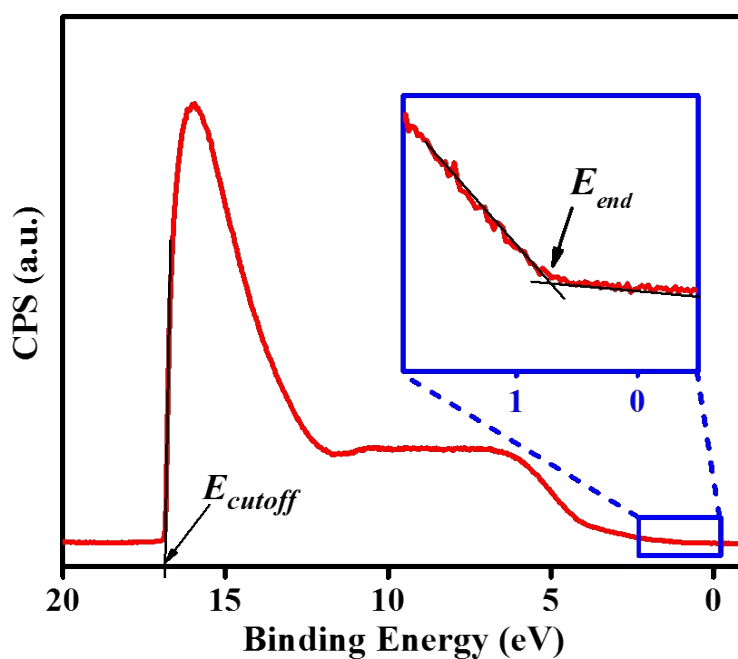


Fig. S8 Ultraviolet photoelectron spectroscopy (UPS) is used to determine the Fermi energy (E_F) and the valence band energy (E_v) level or HOMO. E_F is calculated from the equation: E_F (Fermi energy) = 21.21 eV (He I) - E_{cutoff} . HOMO = $E_F + E_{end}$; LUMO = HOMO - E_g (Band gap).

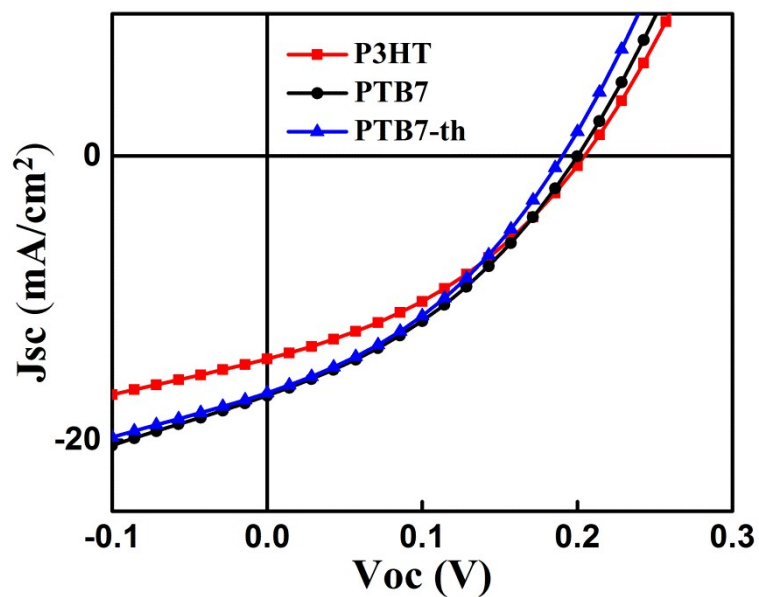


Fig. S9 AgBiS₂ solar cells with P3HT, PTB7, PTB7-th as hole transport layers for comparison.

Table S1 The parameters of AgBiS₂ solar cells with different hole transport layers.

Material	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
P3HT	0.211	15.679	37.466	1.238
PTB7	0.200	16.853	35.605	1.199
PTB7-th	0.190	16.644	36.134	1.144